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STPIC6D595

Power logic 8-bit shift register

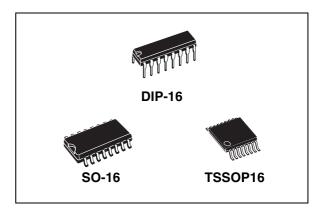
Features

- Low $R_{DS(on)}$: 4 Ω typ
- Eight 100 mA DMOS outputs
- 250 mA current limit capability
- Devices are cascadable
- Low power consumption
- Footprint compatible with STPIC6C595

Description

This STPIC6D595 is a monolithic, mediumvoltage, low current power 8-bit shift register designed for use in systems that require relatively moderate load power such as LEDs.

The device contains an 8-bit serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. Data transfers through both the shift and storage register clock (SRCK) and the register clock (\overline{RCK}), respectively. The device transfers data out the serial output (SER OUT) port on the rising edge of SRCK. The storage register transfers data to the output buffer when shift register clear (CLR) is high. When \overline{CLR} is low, the input shift register is cleared. When output enable (\overline{G}) is held high, all data in the output buffer is held low and all drain output are off. When G is held low, data from the storage register is transparent to the output buffer.



When data in the output buffers is low, the DMOS transistor outputs are off. When data is high, the DMOS transistor outputs have sink-current capability. The SER OUT allows for cascading of the data from the shift register to additional devices.

Output are low-side, open-drain DMOS transistors with output ratings of 20 V and 120 mA continuous sink-current capability. Each output provides a 250 mA maximum current limit at $T_C = 25\,^{\circ}\text{C}$. The current limit decreases as the junction temperature increases for additional device protection. The device also provides up to 2.0 kV of ESD protection when tested using the human-body model.

The STPIC6D595 is characterized for operation over the operating case temperature range of -40 °C to 125 °C.

Table 1. Device summary

Order codes	Package	Packaging
STPIC6D595MTR	SO-16 (Tape and reel)	2500 parts per reel
STPIC6D595TTR	TSSOP16 (Tape and reel)	2500 parts per reel
STPIC6D595B1R	DIP-16	25 parts per tube

Contents STPIC6D595

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1 Logic symbol and pin configuration

Figure 1. Pin configuration

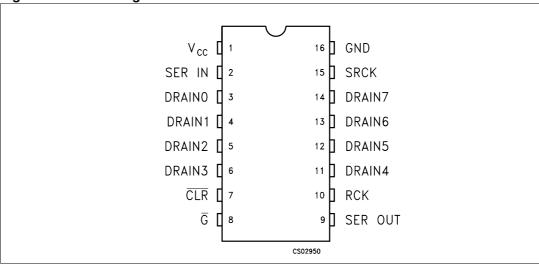
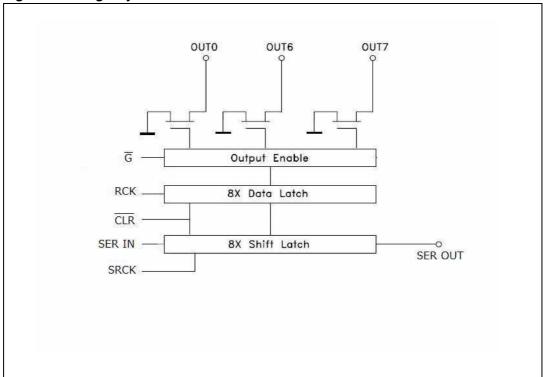


Figure 2. Logic symbol



Maximum rating STPIC6D595

2 Maximum rating

Stressing the device above the rating listed in the "absolute maximum ratings" table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2.1 Absolute maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CC}	Logic supply voltage (See Note 1)	7	V
VI	Logic input voltage range	-0.3 to 7	V
V _{DS}	Power DMOS drain to source voltage (See Note 2)	20	V
I _D	Pulsed drain current, each output, all output ON $(T_C = 25 ^{\circ}C)$	250	mA
I _D	Continuous current, each output, all output ON (T _C = 25 °C)	100	mA
I _D	Peak drain current single output (T _C = 25 °C) (See <i>Note 3</i>)	250	mA
P _d	Continuous total dissipation (T _C ≤ 25 °C)	1087	mW
P _d	Continuous total dissipation (T _C = 125 °C)	217	mW
T _J	Operating virtual junction temperature range	-40 to +150	°C
T _C	Operating case temperature range	-40 to +125	°C
T _{stg}	Storage temperature range	-65 to +150	°C
T _L	Lead temperature 1.6 mm (1/16 inch) from case for 10 seconds	260	°C

2.2 Thermal data

Table 3. Thermal data

Symbol	Parameter	Package	Values	Unit
R _{th(JA)}	Thermal resistance junction-ambient	DIP-16	85	
		SO-16	107	°C/W
		TSSOP16	143	

STPIC6D595 Maximum rating

2.3 Recommended operating conditions

Table 4. Recommended operating conditions

Symbol	Parameter	Min	Max	Unit
V _{CC}	Logic supply voltage	4.5	5.5	V
V _{IH}	High level input voltage	0.85V _{CC}	V _{CC}	V
V_{IL}	Low level input voltage	0	0.15V _{CC}	V
I _{DP}	Pulse drain output current (T _C = 25 °C, V _{CC} = 5 V, all outputs ON) (see <i>Note 3</i> , <i>Note 4</i>)		250	mA
t _{su}	Set-up time, SER IN high before SRCK ↑ (see <i>Figure 4</i> and <i>Figure 8</i>)	10		ns
t _h	Hold time, SER IN high after SRCK ↑ (see Figure 4, Figure 7, Figure 8)	10		ns
t _W	Pulse duration (see Figure 8)	40		ns
T _C	Operating case temperature	-40	125	°C

Electrical characteristics STPIC6D595

3 Electrical characteristics

3.1 DC characteristics

 V_{CC} = 5 V, T_{C} = 25 °C, unless otherwise specified.

Table 5. DC characteristics

Symbol	Parameter	Test conditions Mi		Тур	Max	Unit
V _{(BR)DSX}	Drain-to-source breakdown voltage	I _D = 1 mA			20	V
V _{SD}	Source-to-drain diode forward voltage	I _F = 100 mA		0.85	1.2	V
V.	High level output	$I_{OH} = -20 \mu A V_{CC} = 4.5 V$	4.4	4.49		V
V _{OH}	voltage SER OUT	I_{OH} = -4 mA V_{CC} = 4.5 V	4			V
V.	Low level output	$I_{OH} = 20 \mu A V_{CC} = 4.5 V$		1	100	mV
V _{OL}	voltage SER OUT	$I_{OH} = 4 \text{ mA } V_{CC} = 4.5 \text{ V}$		145	300	mV
I _{IH}	High level input current	$V_{CC} = 5.5 V V_I = V_{CC}$		1	100	nA
I _{IL}	Low level input current	$V_{CC} = 5.5 \text{ V } V_{I} = 0$		-1	-100	nA
I _{CC}	Logic supply current	$V_{CC} = 5.5 \text{ V}$ All outputs OFF or ON		23	40	μА
I _{CC(FRQ)}	Logic supply current at frequency	$f_{SRCK} = 5 \text{ MHz } C_L = 30 \text{ pF}$ All outputs OFF (See <i>Figure 6</i> , ⁽¹⁾)	80 pF		250	μА
I _N	Nominal current	$V_{DS(on)} = 0.5 \text{ VI}_{N} = I_{D}$ $T_{C} = 85 ^{\circ}\text{C}$ (See <i>Note 4</i> , <i>Note 5</i> , <i>Note 6</i>)	; = 85 °C		200	mA
		$V_{DS} = 20 \text{ V } V_{CC} = 5.5 \text{ V or } 0 \text{ V}$		0.02	1	μΑ
I _{DSX}	Off-state drain current	$V_{DS} = 20 \text{ V } V_{CC} = 5.5 \text{ V or } 0 \text{ V}$ $T_C = 125 \text{ °C}$		0.5	1	μА
	Static drain source on	$I_D = 50 \text{ mA V}_{CC} = 4.5 \text{ V}$		3.4	4	Ω
R _{DS(on)}	state resistance (See <i>Note 4</i> , and	$I_D = 50 \text{ mA V}_{CC} = 4.5 \text{ V}$ $T_C = 125 \text{ °C}$		4.8	6	Ω
	Note 5)	I _D = 100 mA V _{CC} = 4.5 V	_	3.5	6	Ω

^{1.} Not tested, specified by design

3.2 Switching characteristics

 V_{CC} = 5 V, T_{C} = 25 °C, unless otherwise specified.

Table 6. Switching characteristics

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
t _{PHL}	Propagation delay time, high to low level output from \overline{G}		-	19	30	ns
t _{PLH}	Propagation delay time, low to high level output from $\overline{\mathbf{G}}$		1	46	70	ns
t _{PHL-SDO}	Propagation delay time, clock to SDO		ı	19	25	ns
t _{PLH-SDO}	Propagation delay time, clock to SDO	C = 20 pE = 75 mA	1	46	60	ns
t _{PLH-R_O}	Propagation delay low to high level RCK to OUT	$C_L = 30 \text{ pF I}_D = 75 \text{ mA}$ (See Figure 4, Figure 5, Figure 6,	-	62	90	ns
t _{PHL-R_O}	Propagation delay high to low level RCK to OUT	Figure 7,)	ı	13	18	ns
t _{PLH-S_SO}	Propagation delay low to high level SCK to SDO		ı	14	20	ns
t _{PHL-S_SO}	Propagation delay high to low level SCK to SDO		-	14	20	ns
t _r	Rise time, drain output		-	20	30	ns
t _f	Fall time, drain output		-	15	20	ns

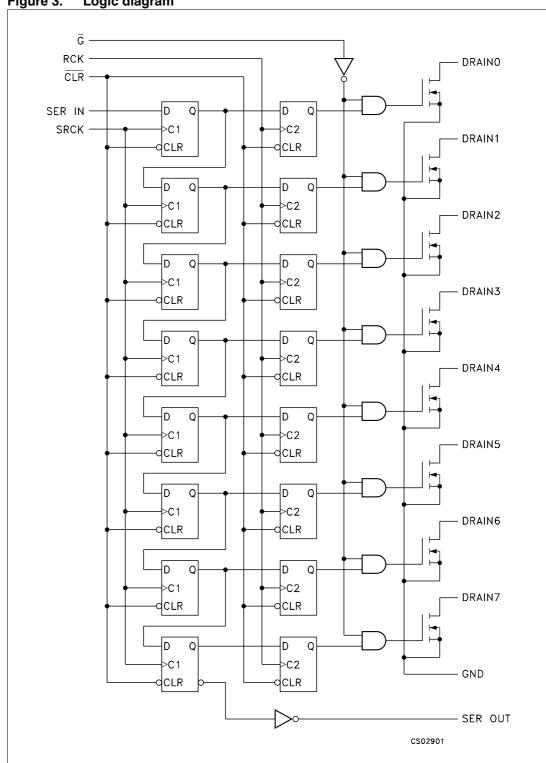
Note:

- 1 All voltage value are with respect to GND
- 2 Each power DMOS source is internally connected to GND
- 3 Pulse duration \leq 100 μ s and duty cycle \leq 2%
- 4 Technique should limit T_J T_C to 10 °C maximum
- 5 These parameters are measured with voltage sensing contacts separate from the currentcarrying contacts.
- Nominal Current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at $T_C = 85$ °C.

Logic diagram STPIC6D595

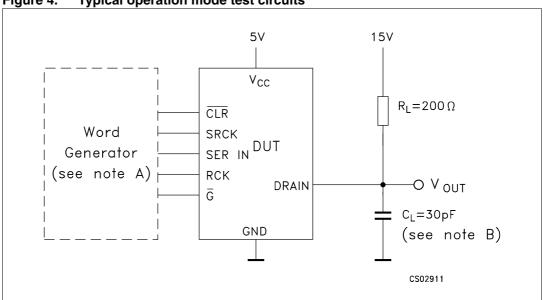
Logic diagram 4



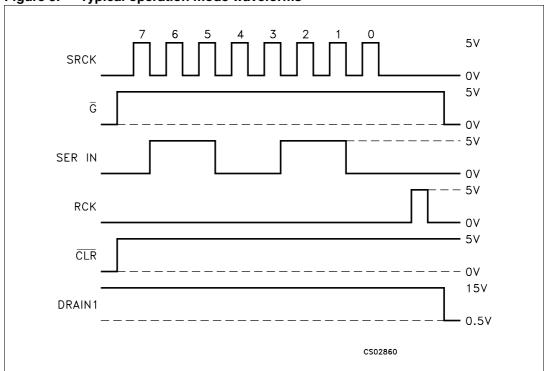


Typical operating circuit 5

Figure 4. Typical operation mode test circuits







A) The word generator has the following characteristics: $t_r \le 10$ ns, $t_f \le 10$ ns, $t_W = 300$ ns, Note: pulse repetition rate (PRR) = 5 kHz, Z_O = 50 Ω

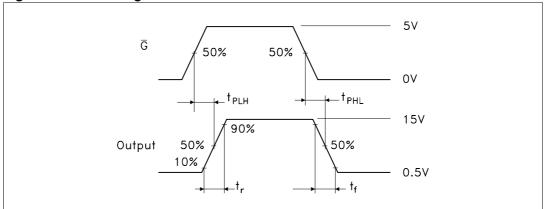
B) C_L includes probe and jig capacitance.

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5٧ 15V v_{cc} $R_L = 200 \,\Omega$ $\overline{\text{CLR}}$ Word SRCK SER IN DUT Generator (see note A) RCK O V OUT DRAIN $\bar{\mathsf{G}}$ $C_L = 30pF$ GND (see note B)

Figure 6. Typical operation mode test circuits





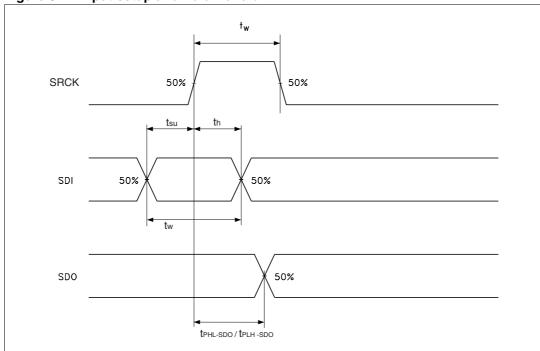


Figure 8. Input setup and hold waveform

Note: 1 A) The word generator has the following characteristics: $t_r \le 10$ ns, $t_f \le 10$ ns, $t_W = 300$ ns, pulse repetition rate (PRR) = 5 kHz, $Z_O = 50~\Omega$

2 B) C_L includes probe and jig capacitance.

Figure 9. Input equivalent circuit

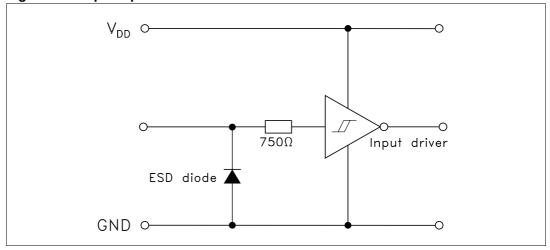
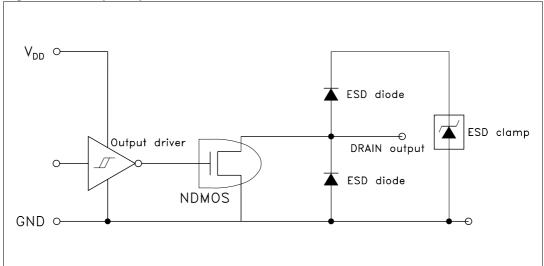


Figure 10. Output equivalent circuit

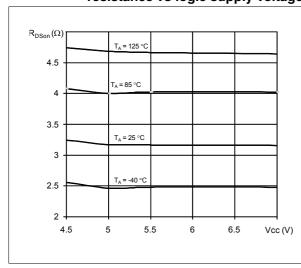


6 Typical performance and characteristics

Unless otherwise specified $T_J = 25$ °C

Figure 11. Static drain-source on-state resistance vs logic supply voltage

Figure 12. Supply current vs frequency



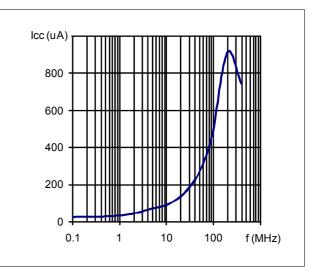
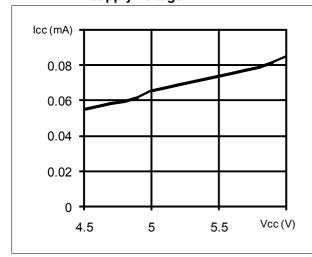
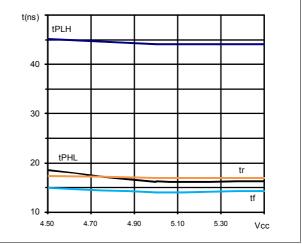


Figure 13. Supply current vs supply voltage

Figure 14. Switching time vs case temperature





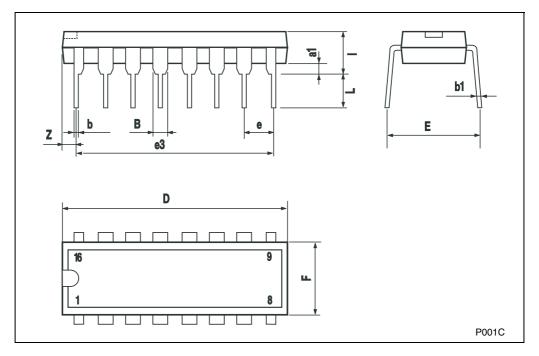
7 Package mechanical data

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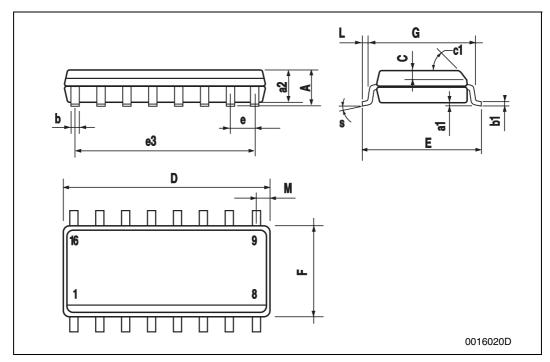
Plastic DIP-16 (0.25) MECHANICAL DATA

DIM		mm.			inch		
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
a1	0.51			0.020			
В	0.77		1.65	0.030		0.065	
b		0.5			0.020		
b1		0.25			0.010		
D			20			0.787	
E		8.5			0.335		
е		2.54			0.100		
e3		17.78			0.700		
F			7.1			0.280	
I			5.1			0.201	
L		3.3			0.130		
Z			1.27			0.050	



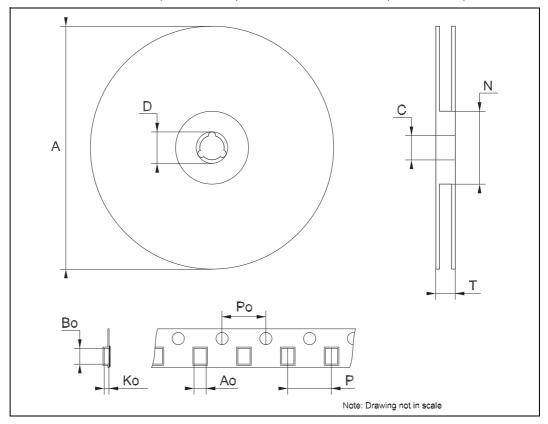
SO-16 MECHANICAL DATA

DIM		mm.			inch		
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А			1.75			0.068	
a1	0.1		0.25	0.004		0.010	
a2			1.64			0.063	
b	0.35		0.46	0.013		0.018	
b1	0.19		0.25	0.007		0.010	
С		0.5			0.019		
c1			45°	(typ.)			
D	9.8		10	0.385		0.393	
Е	5.8		6.2	0.228		0.244	
е		1.27			0.050		
e3		8.89			0.350		
F	3.8		4.0	0.149		0.157	
G	4.6		5.3	0.181		0.208	
L	0.5		1.27	0.019		0.050	
М			0.62			0.024	
S		•	8° (max.)	•	•	



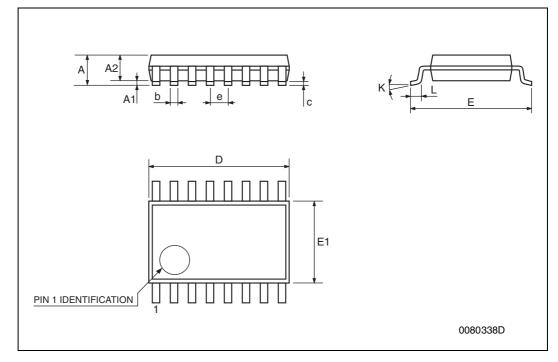
Tape & Reel SO-16 MECHANICAL DATA

DIM.	mm.			inch		
Dilvi.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А			330			12.992
С	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
Т			22.4			0.882
Ao	6.45		6.65	0.254		0.262
Во	10.3		10.5	0.406		0.414
Ko	2.1		2.3	0.082		0.090
Po	3.9		4.1	0.153		0.161
Р	7.9		8.1	0.311		0.319

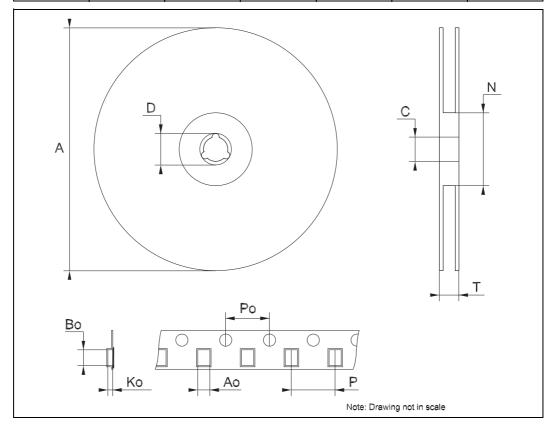


TSSOP16 MECHANICAL DATA

DIM.	mm.			inch		
DIWI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
С	0.09		0.20	0.004		0.0079
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
е		0.65 BSC			0.0256 BSC	
К	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А			330			12.992
С	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
Т			22.4			0.882
Ao	6.7		6.9	0.264		0.272
Во	5.3		5.5	0.209		0.217
Ko	1.6		1.8	0.063		0.071
Po	3.9		4.1	0.153		0.161
Р	7.9		8.1	0.311		0.319



Revision history STPIC6D595

8 Revision history

Table 7. Document revision history

Date	Revision	Changes	
20-Jun-2007	1	First release	
06-Sep-2007	2	Change from Preliminary to final version	
17-Nov-2009	3	Updated: Table 2, Table 3, Table 5, Table 6, Table 6, Figure 1, Figure 7, Figure 8 and Figure 9 Added: Figure 2, Figure 11, Figure 12, Figure 13 and Figure 14	

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